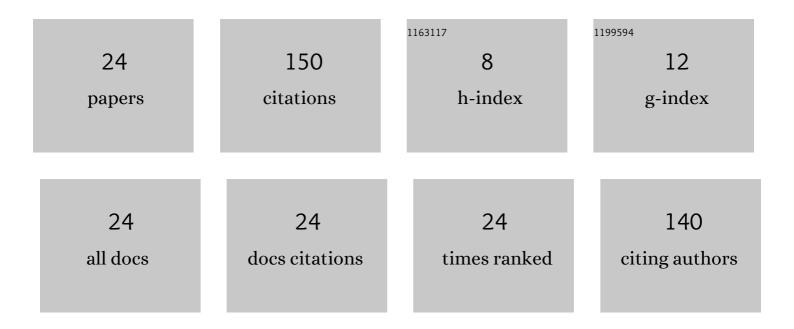
Zhongliang Qiao

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Modal gain characteristics of a 2 <i>μ</i> m InGaSb/AlGaAsSb passively mode-locked quantum well laser. Applied Physics Letters, 2017, 111, .	3.3	20
2	Compact silicon photonic hybrid ring external cavity (SHREC)/InGaSb-AlGaAsSb wavelength-tunable laser diode operating from 1881-1947â€nm. Optics Express, 2020, 28, 5134.	3.4	17
3	Sub-kHz linewidth, hybrid III-V/silicon wavelength-tunable laser diode operating at the application-rich 1647-1690â€nm. Optics Express, 2020, 28, 25215.	3.4	14
4	Design and Analysis of 2-μm InGaSb/GaSb Quantum Well Lasers Integrated Onto Silicon-on-Insulator (SOI) Waveguide Circuits Through an Al2O3 Bonding Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2016, 22, 16-22.	2.9	13
5	Investigation of regime switching from mode locking to Q-switching in a 2 µm InGaSb/AlGaAsSb quantum well laser. Optics Express, 2018, 26, 8289.	3.4	13
6	1 × N (N = 2, 8) Silicon Selector Switch for Prospective Technologies at the 2 μm Waveband. IEEE Photonics Technology Letters, 2020, 32, 1127-1130.	2.5	12
7	High-performance 1.06- <i>μ</i> m InGaAs/GaAs double-quantum-well semiconductor lasers with asymmetric heterostructure layers. Semiconductor Science and Technology, 2019, 34, 055013.	2.0	9
8	High temperature characteristics of a 2 <i>μ</i> m InGaSb/AlGaAsSb passively mode-locked quantum well laser. Applied Physics Letters, 2019, 114, .	3.3	8
9	Wafer-Scale Demonstration of Low-Loss (â^1⁄40.43 dB/cm), High-Bandwidth (>38 GHz), Silicon Photonics Platform Operating at the C-Band. IEEE Photonics Journal, 2022, 14, 1-9.	2.0	8
10	Research on Narrow Linewidth External Cavity Semiconductor Lasers. Crystals, 2022, 12, 956.	2.2	8
11	Direct parameter extraction method for InP heterojunction bipolar transistors based on the combination of T- and π-models up to 110 GHz. Semiconductor Science and Technology, 2020, 35, 025001.	2.0	5
12	Imaging the defect distribution in 2D hexagonal boron nitride by tracing photogenerated electron dynamics. Journal Physics D: Applied Physics, 2020, 53, 405106.	2.8	5
13	Temperature- and current-dependent spontaneous emission study on 2 Âμm InGaSb/AlGaAsSb quantum well lasers. Japanese Journal of Applied Physics, 2017, 56, 050310.	1.5	4
14	Analysis of Compact Silicon Photonic Hybrid Ring External Cavity (SHREC) Wavelength-Tunable Laser Diodes Operating From 1881–1947 nm. IEEE Journal of Quantum Electronics, 2020, 56, 1-11.	1.9	4
15	Research on Silicon-Substrate-Integrated Widely Tunable, Narrow Linewidth External Cavity Lasers. Crystals, 2022, 12, 674.	2.2	3
16	Temperature-dependent phase noise properties of a two-section GaSb-based mode-locked laser emitting at 2 1¼m. Applied Physics Letters, 2020, 117, 141103.	3.3	2
17	The design of 1 $ ilde{A}$ — 2 MMI at the MIR wavelength of 2 μm. , 2019, , .		1
18	Stable Mode-Locked Operation With High Temperature Characteristics of a Two-Section InGaAs/GaAs Double Quantum Wells Laser. IEEE Access, 2021, 9, 16608-16614.	4.2	1

#	Article	IF	CITATIONS
19	Compact, Hybrid III-V/Silicon Vernier Laser Diode Operating From 1955–1992 nm. IEEE Photonics Journal, 2021, 13, 1-5.	2.0	1
20	Mode-locked operation characteristics of a monolithic integrated two-section InGaAs/GaAs double quantum wells laser with asymmetric waveguide. Optics and Laser Technology, 2022, 147, 107702.	4.6	1
21	Modal gain characteristics of a two-section InGaAs/GaAs double quantum well passively mode-locked laser with asymmetric waveguide. Scientific Reports, 2022, 12, 5010.	3.3	1
22	Silicon Nitride Waveguiding for Prospective Technologies at the 2 Î $^1\!\!/4$ m Waveband. , 2019, , .		0
23	Two-mode multiplexer based on the multilayer Si-SiN platform for $2\hat{l}$ 4m waveband. , 2019, , .		0
24	All-Solid-State DUV Light Source by Quadrupling of an Acousto-Optically Q-Switched Nd:YVO ₄ Laser. IEEE Access, 2021, 9, 165989-165995.	4.2	0